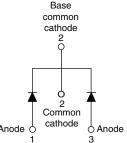




Vishay Semiconductors

Ultrafast Rectifier, 10 A FRED Pt®





	Ba com cath	mon ode	
Anode O	Com) 2 Imon node	Anode

PRODUCT SUMMARY						
Package	TO-220AB					
I _{F(AV)}	2 x 5 A					
V_{R}	200 V					
V _F at I _F	0.87 V					
t _{rr} typ.	See Recovery table					
T _J max.	175 °C					
Diode variation	Common cathode					

FEATURES

- Ultrafast recovery time
- · Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- and qualified Designed according JEDĔC®-JESD 47
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





HALOGEN **FREE**

DESCRIPTION / APPLICATIONS

VS-MUR.. series are the state of the art ultrafast recovery rectifiers specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER		SYMBOL	TEST CONDITIONS	MAX.	UNITS				
Peak repetitive reverse voltage		V_{RRM}		200	V				
Average restified forward surrent	er leg	I _{F(AV)}		5					
Average rectified forward current total c	device		Rated V _R , T _C = 149 °C	10					
Non-repetitive peak surge current per leg		I _{FSM}		50	Α				
Peak repetitive forward current per leg		I _{FM}	Rated V_R , square wave, 20 kHz $T_C = 149 ^{\circ}C$	10					
Operating junction and storage temperatures		T _J , T _{Stg}		-65 to +175	°C				

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	TEST CONDITIONS MIN. TYP. MAX.					
Breakdown voltage, blocking voltage	V _{BR} , V _R	Ι _R = 100 μΑ	200	-	-			
Forward voltage	V _F	I _F = 5 A, T _J = 125 °C	-	0.87	0.99	V		
		I _F = 10 A, T _J = 125 °C	-	1.02	1.20			
		I _F = 10 A	-	1.12	1.25			
Payaraa laakaga aurrant	,	V _R = V _R rated	-	-	10			
Reverse leakage current I _R		T _J = 150 °C, V _R = V _R rated	-	-	250	μA		
Junction capacitance	C _T	V _R = 200 V	-	8	-	pF		
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH		



VS-MUR1020CTPbF, VS-MUR1020CT-N3

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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS				
Reverse recovery time		$I_F = 1.0 \text{ A, } dI_F/dt =$	$50 \text{ A/}\mu\text{s}, \text{ V}_{\text{R}} = 30 \text{ V}$	-	-	35				
		I _F = 0.5 A, I _R = 1.0 A, I _{REC} = 0.25 A		-	-	25	ns			
	t _{rr}	T _J = 25 °C	$I_F = 5 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$	-	24	-	115			
		T _J = 125 °C		-	35	-				
Peak recovery current	I _{RRM}	T _J = 25 °C		-	3.3	-	۸			
		IRRM	IRRM	IRRM	IRRM	IRRM T	T _J = 125 °C	$V_{R} = 160 \text{ V}$	-	5.0
Reverse recovery charge	0	T _J = 25 °C	-n3 •	-	33	-	nC			
	Q _{rr}	T _J = 125 °C		-	76	-	110			

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C	
Thermal resistance, junction to case per leg	R _{thJC}		-	-	5		
Thermal resistance, junction to ambient per leg	R _{thJA}		-	-	50	°C/W	
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-		
Weight			-	2.0	-	g	
Weight			-	0.07	-	OZ.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style TO-220AB		MUR1	020CT		

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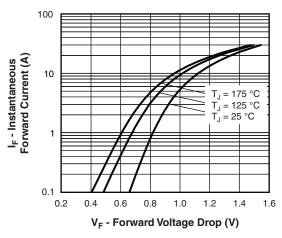


Fig. 1 - Typical Forward Voltage Drop Characteristics

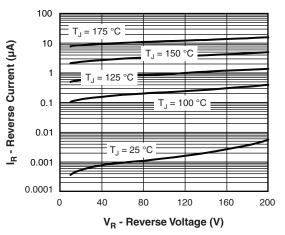


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

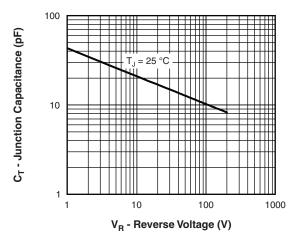


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

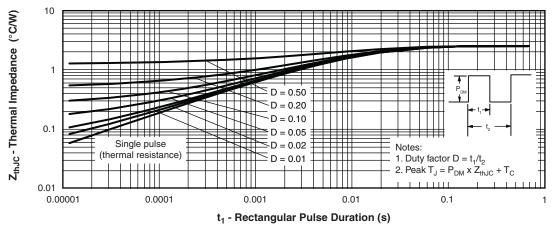


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics





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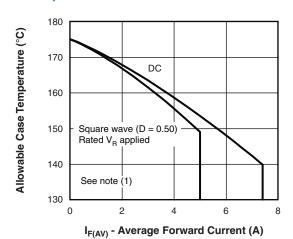


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

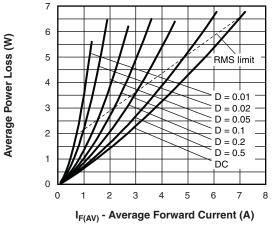


Fig. 6 - Forward Power Loss Characteristics

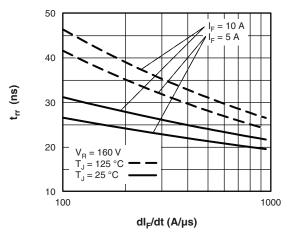


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

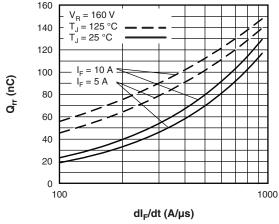


Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

 $\begin{array}{l} \text{(1)} \ \ \text{Formula used:} \ T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \ \text{at} \ (I_{F(AV)}/D) \ (\text{see fig. 6}); \\ Pd_{REV} = \text{Inverse power loss} = V_{R1} \times I_R \ (1 - D); \ I_R \ \text{at} \ V_{R1} = \text{Rated} \ V_R \\ \end{array}$

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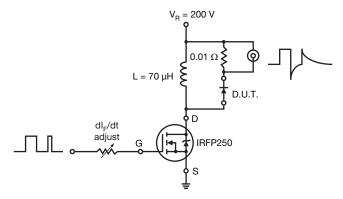
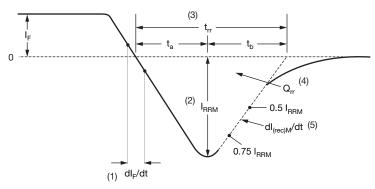


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dI_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $t_{\rm rr}$ reverse recovery time measured from zero crossing point of negative going $I_{\rm F}$ to point where a line passing through 0.75 $I_{\rm RRM}$ and 0.50 $I_{\rm RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) dl_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

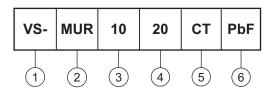
Fig. 10 - Reverse Recovery Waveform and Definitions

VS-MUR1020CTPbF, VS-MUR1020CT-N3

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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Ultrafast MUR series

Current rating (10 = 10 A)

Voltage rating (20 = 200 V)

CT = center tap (dual) TO-220/D²PAK/TO-262

6 - Environmental digit:

PbF = lead (Pb)-free and RoHS-compliant

-N3 = halogen-free, RoHS-compliant and totally lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-MUR1020CTPbF	50	1000	Antistatic plastic tube				
VS-MUR1020CT-N3	50	1000	Antistatic plastic tube				

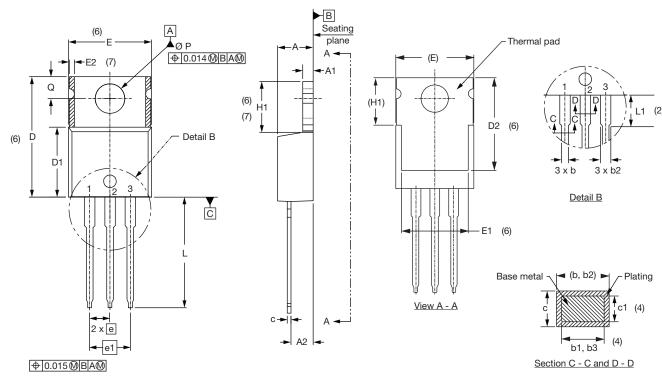
LINKS TO RELATED DOCUMENTS						
Dimensions <u>www.vishay.com/doc?95222</u>						
Dout moulding information	TO-220ABPbF	www.vishay.com/doc?95225				
Part marking information	TO-220AB-N3	www.vishay.com/doc?95028				



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TO-220AB

DIMENSIONS in millimeters and inches



Lead assignments

<u>Diodes</u>

- 1. Anode/open
- 2. Cathode
- 3. Anode

Conforms to JEDEC outline TO-220AB

SYMBOL	MILLIMETERS		INCHES		NOTES
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

SYMBOL	MILLIMETERS		INCHES		INCHES		NOTES
STIVIBOL	MIN.	MAX.	MIN.	MAX.	NOTES		
E	10.11	10.51	0.398	0.414	3, 6		
E1	6.86	8.89	0.270	0.350	6		
E2	-	0.76	-	0.030	7		
е	2.41	2.67	0.095	0.105			
e1	4.88	5.28	0.192	0.208			
H1	6.09	6.48	0.240	0.255	6, 7		
L	13.52	14.02	0.532	0.552			
L1	3.32	3.82	0.131	0.150	2		
ØΡ	3.54	3.73	0.139	0.147			
Q	2.60	3.00	0.102	0.118			
θ	90° to 93°		90° to 93°				

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline

Lead tip



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